NSN 5962-01-361-0692

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view Online at https://aerobasegroup.com/hsn/baoz-01-361-0692
Body Length:
Between 0.342 inches and 0.358 inches
Body Width:
Between 0.342 inches and 0.358 inches
Body Height:
Between 0.060 inches and 0.100 inches
Maximum Power Dissipation Rating:
300.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and burn in and monolithic and programmed and electrostatic sensitive
Inclosure Material:
Ceramic
Inclosure Configuration:
Leadless flat pack
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
C-2 mil-m-38510
Current Rating Per Characteristic:
50.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
And-or invert gate array
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 12.0 volts power source
Time Rating Per Chacteristic:
75.00 nanoseconds delay
Memory Device Type:
Pal
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)
Terminal Type And Quantity:
20 leadless

N/a

Shelf Life:

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Demilitarization:

Yes - demil/mli

Fiig:

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